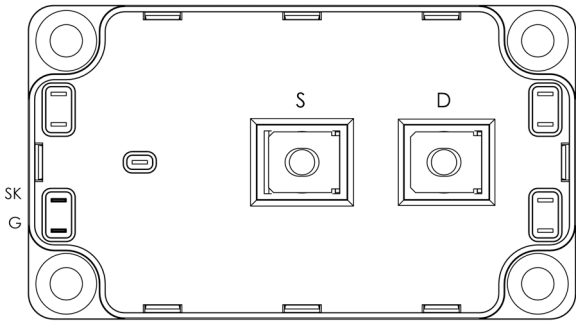
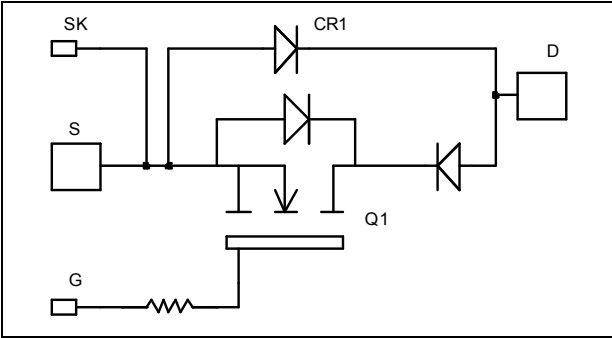


Single switch
Series & parallel diodes
MOSFET Power Module

$V_{DSS} = 500V$
 $R_{DSon} = 13m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 335A$ @ $T_c = 25^\circ C$



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	335
		$T_c = 80^\circ C$	250
I_{DM}	Pulsed Drain current	1340	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	15	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	3290
I_{AR}	Avalanche current (repetitive and non repetitive)	71	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$			400	μA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 167.5A$		13	15	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 20mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 300	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{iss}	Input Capacitance	$V_{GS} = 0V$		42.2		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		8.24		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$		800		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 250V$		200		
Q_{gd}	Gate – Drain Charge	$I_D = 335A$		420		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 335A$ $R_G = 0.8\Omega$		21		ns
T_r	Rise Time			42		
$T_{d(off)}$	Turn-off Delay Time			96		
T_f	Fall Time			100		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 335A, R_G = 0.8\Omega$		4		mJ
E_{off}	Turn-off Switching Energy			4.16		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 335A, R_G = 0.8\Omega$		6.32		mJ
E_{off}	Turn-off Switching Energy			4.64		
R_{thJC}	Junction to Case Thermal Resistance				0.038	$^{\circ}C/W$

Series diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$			150	μA
I_F	DC Forward Current	$T_c = 80^{\circ}C$		360		A
V_F	Diode Forward Voltage	$I_F = 360A$		1.7	2.5	V
		$I_F = 720A$		2		
		$I_F = 360A, T_j = 125^{\circ}C$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 360A$ $V_R = 400V$ $di/dt = 1200A/\mu s$	$T_j = 25^{\circ}C$	70		ns
			$T_j = 125^{\circ}C$	140		
Q_{rr}	Reverse Recovery Charge	$I_F = 360A$ $V_R = 400V$ $di/dt = 1200A/\mu s$	$T_j = 25^{\circ}C$	0.6		μC
			$T_j = 125^{\circ}C$	4.2		
R_{thJC}	Junction to Case Thermal Resistance				0.16	$^{\circ}C/W$

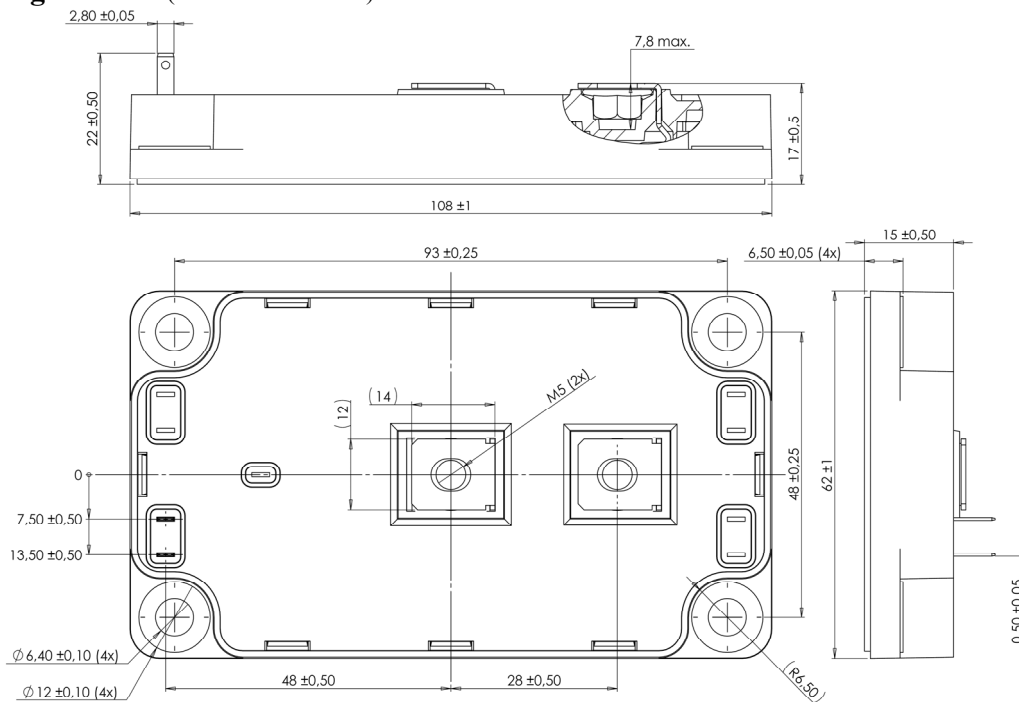
Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V			150	μA
I _F	DC Forward Current	T _c = 80°C		360		A
V _F	Diode Forward Voltage	I _F = 360A		1.7	2.5	V
		I _F = 720A		2		
		I _F = 360A	T _j = 125°C	1.4		
t _{rr}	Reverse Recovery Time	I _F = 360A V _R = 400V di/dt = 1200A/μs	T _j = 25°C	70		ns
			T _j = 125°C	140		
Q _{rr}	Reverse Recovery Charge	I _F = 360A V _R = 400V di/dt = 1200A/μs	T _j = 25°C	0.6		μC
			T _j = 125°C	4.2		
R _{thJC}	Junction to Case Thermal Resistance				0.16	°C/W

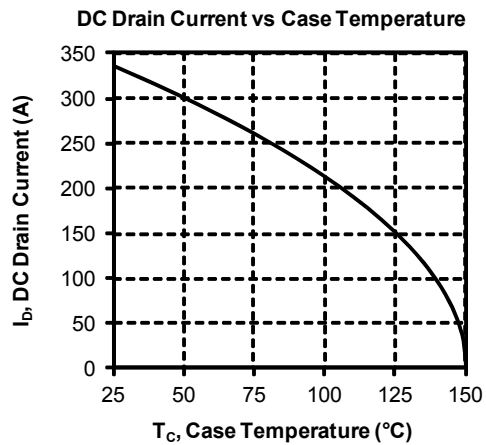
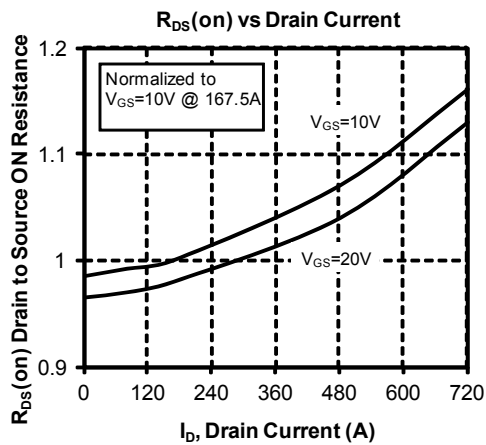
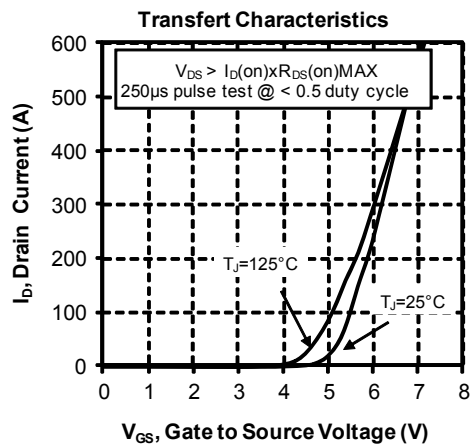
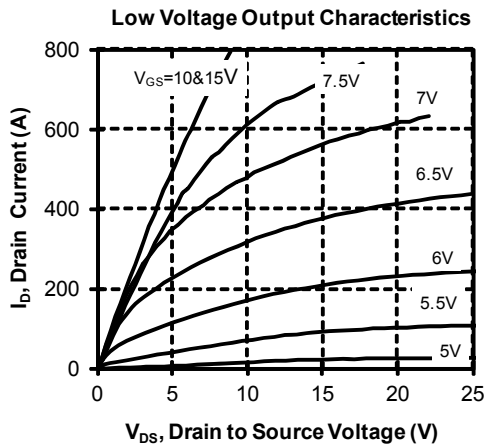
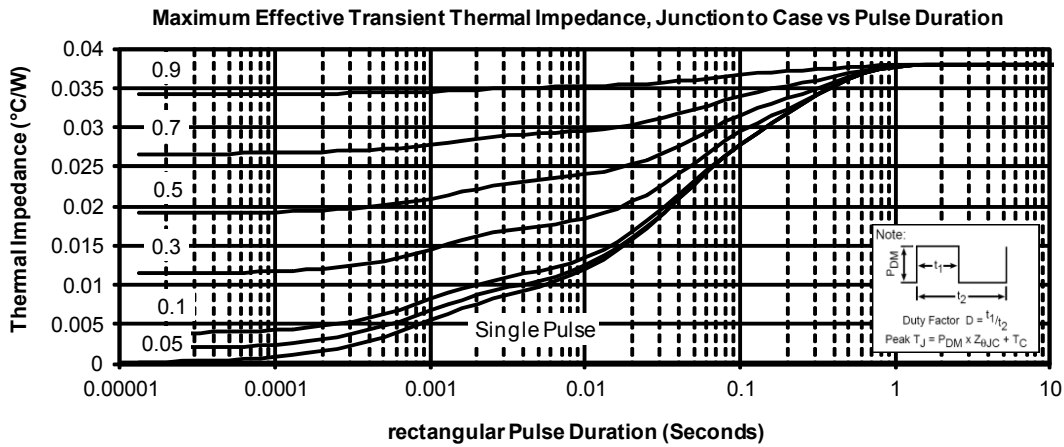
Thermal and package characteristics

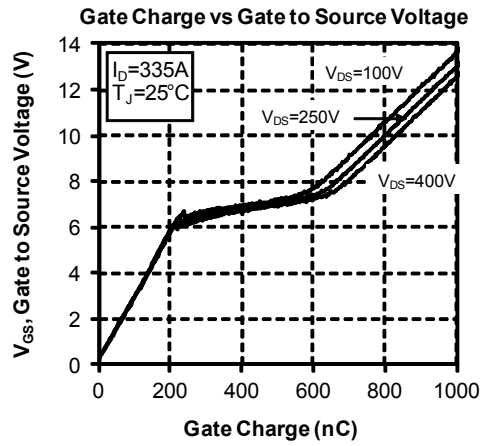
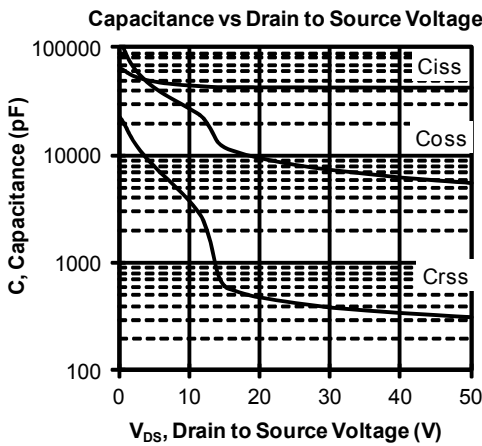
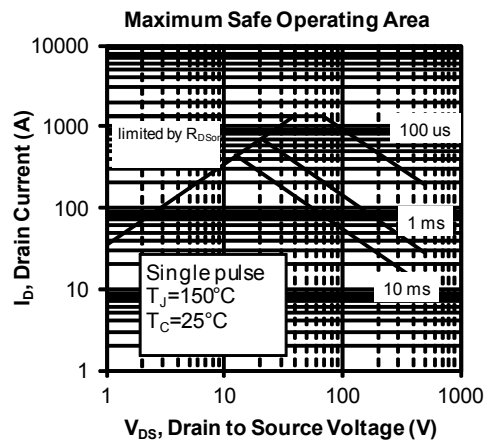
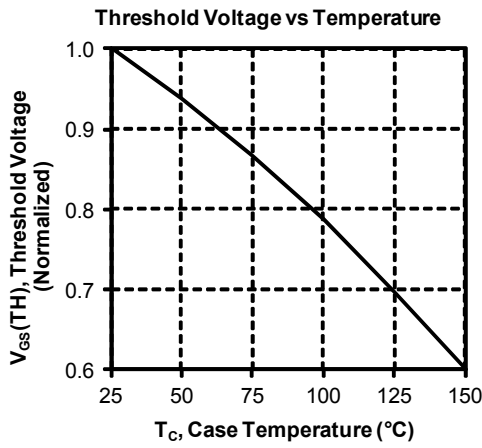
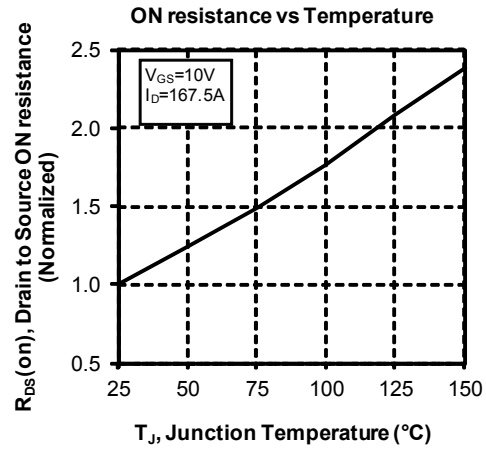
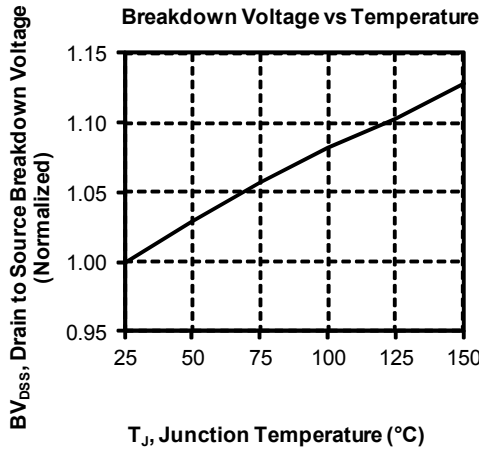
Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	150	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	100			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

SP6 Package outline (dimensions in mm)

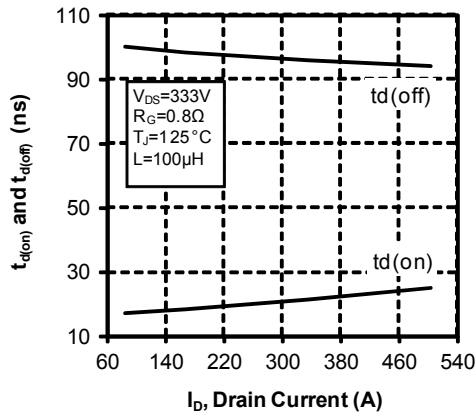


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

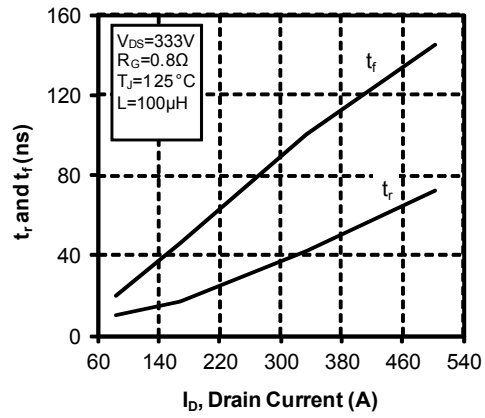
Typical Performance Curve




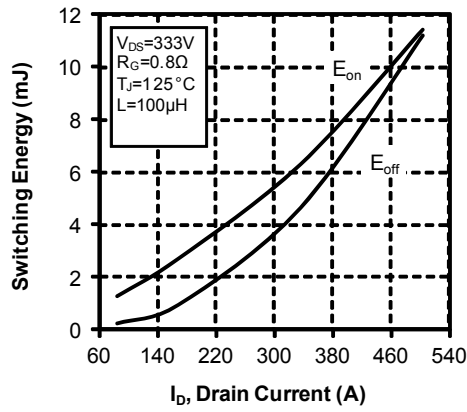
Delay Times vs Current



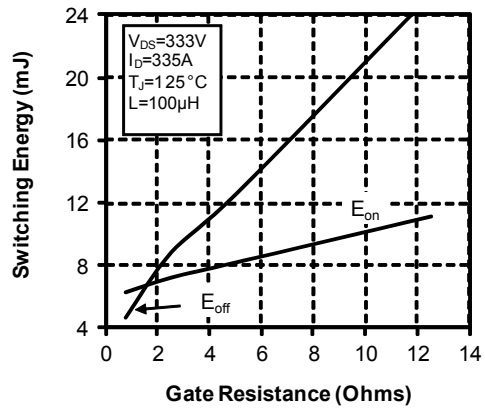
Rise and Fall times vs Current



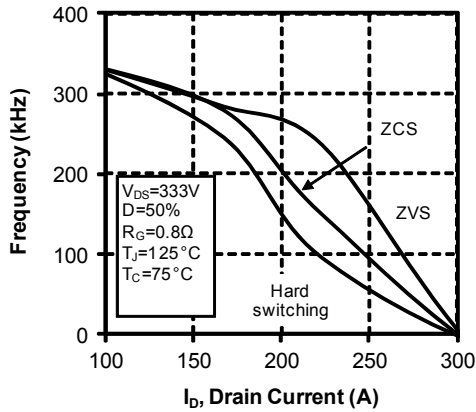
Switching Energy vs Current



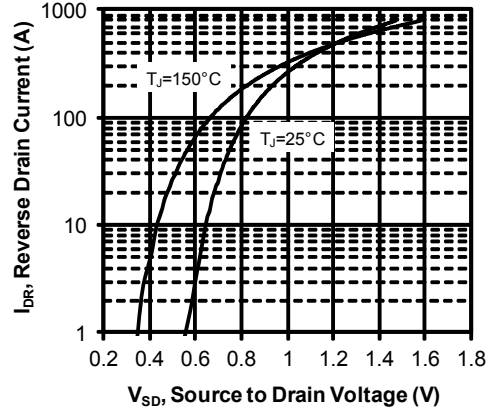
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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